





Phase Control Thyristor

DS5767-3 February 2014 (LN31297)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR1840Y85* DCR1840Y80 DCR1840Y75 DCR1840Y70	8500 8000 7500 7000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, \ V_{RRM} \ t_p = 10\text{ms}, \\ V_{DSM} \ \& \ V_{RSM} &= \\ V_{DRM} \ \& \ V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. *8200V @ -40° C, 8500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1840Y85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
$I_{T(AV)}$	1840A
I _{TSM}	25000A
dV/dt*	1500V/µs
dI/dt	300A/μs

* Higher dV/dt selections available

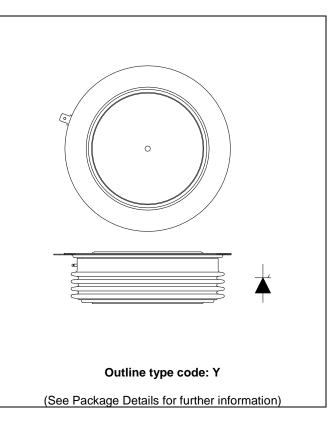


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	1840	А
I _{T(RMS)}	RMS value	-	2890	А
I _T	Continuous (direct) on-state current	-	2770	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	25.0	kA
l ² t	I ² t for fusing	$V_R = 0$	3.125	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.00835	°C/W
		Single side cooled	Anode DC	-	0.0134	°C/W
			Cathode DC	-	0.023	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 54.0kN	Double side	-	0.002	°C/W
		(with mounting compound)	Single side	-	0.004	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			48	59	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dI/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125$ °C				
V _{T(TO)}	Threshold voltage – Low level	100A to1000A at T _{case} = 125	°C	-	0.9	٧
	Threshold voltage – High level	1000A to 7200A at T _{case} = 12	25°C	-	1.3	V
r _T	On-state slope resistance – Low level	100A to 1000A at T _{case} = 125°C		-	0.888	mΩ
	On-state slope resistance – High level	1000A to 7200A at T _{case} = 125°C		-	0.55	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
t _q	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ μ s,		-	1200	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$, $T_j = 125$ °C, $dI/dt - 1A/\mu s$,		4800	8000	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
l _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I _T = 5A	-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	400	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	15	mA

CURVES

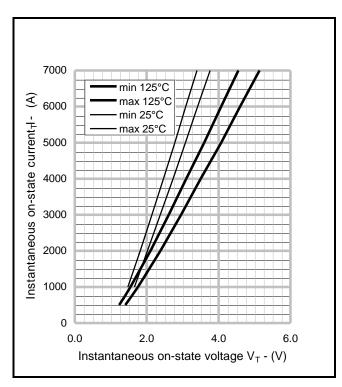


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION Where A = 0.398265

 $V_{TM} = A + Bln (I_T) + C.I_T + D. \sqrt{I_T} \\ B = 0.121095 \\ C = 0.000524$

D = -0.000007

these values are valid for $T_j = 125$ °C for $I_T 500A$ to 7200A

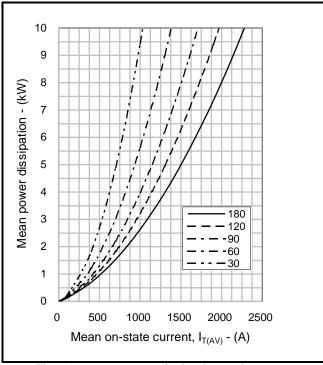


Fig.3 On-state power dissipation - sine wave

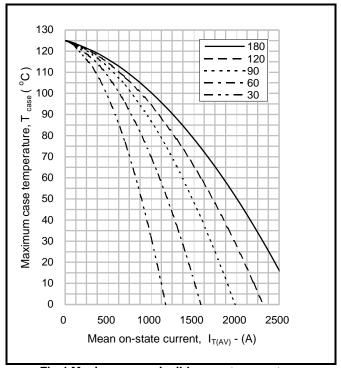


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

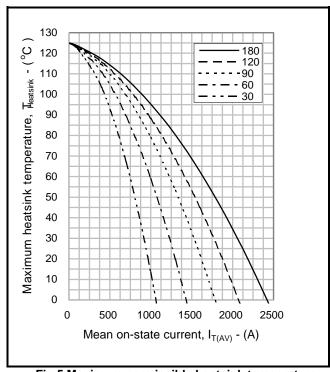


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

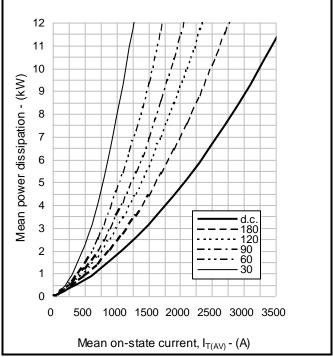
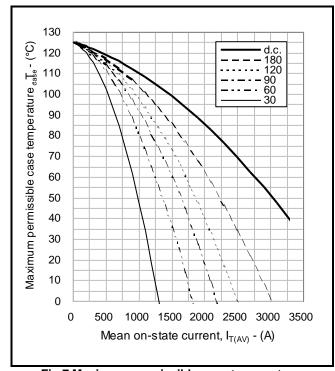
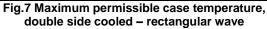


Fig.6 On-state power dissipation - rectangular wave







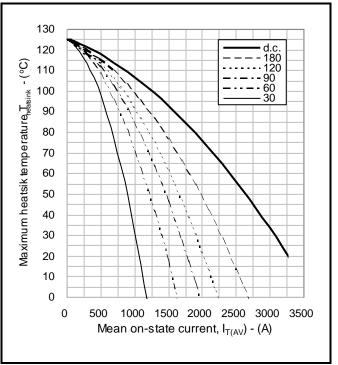
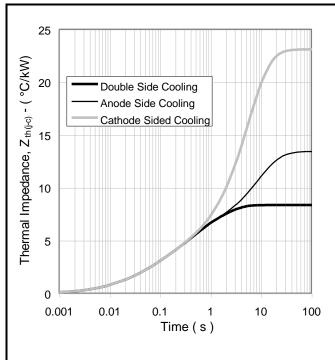


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	0.612	1.7721	3.1053	2.8608
	T _i (s)	0.010332	0.056415	0.333082	1.6323
Anode side cooled	R _i (°C/kW)	0.7009	1.9388	3.61	7.1383
	T _i (s)	0.011328	0.065993	0.419695	9.0612
Cathode side coole	R _i (°C/kW)	0.6728	2.0168	1.7306	18.6391
	T _i (s)	0.010954	0.065544	0.30379	5.7274

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))] [1]$

 $\Delta R_{\text{th(j-c)}}$ Conduction

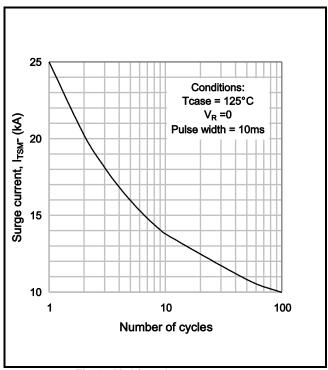
Tables show the increments of thermal resistance $R_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

Double side cooling			
	$\Delta Z_{th}(z)$		
θ°	sine.	rect.	
180	0.94	0.65	
120	1.09	0.92	
90	1.24	1.07	
60	1.38	1.23	
30	1.49	1.40	
15	1 54	1 49	

Αı	Anode Side Cooling				
	ΔZ_t	_h (z)			
θ°	sine.	rect.			
180	0.94	0.64			
120	1.08	0.91			
90	1.23	1.06			
60	1.37	1.22			
30	1.47	1.38			
15	1 52	1 47			

Cath	thode Sided Cooling			
	ΔZ_{th} (z)			
θ° sine.		rect.		
180	0.94	0.64		
120	1.08	0.91		
90	1.24	1.06		
60	1.37	1.22		
30	1.48	1.39		
15	1 53	1 48		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)





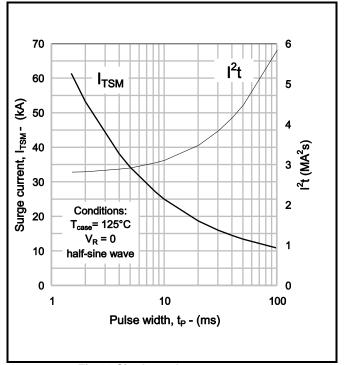


Fig.11 Single-cycle surge current

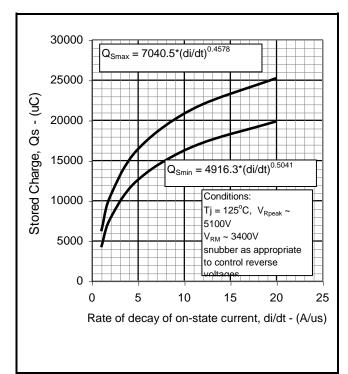


Fig.12 Stored charge

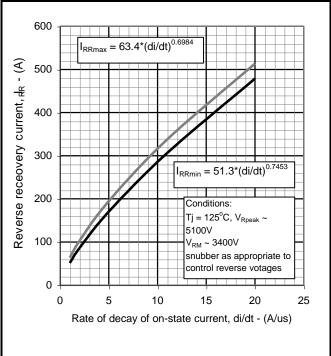


Fig.13 Reverse recovery current

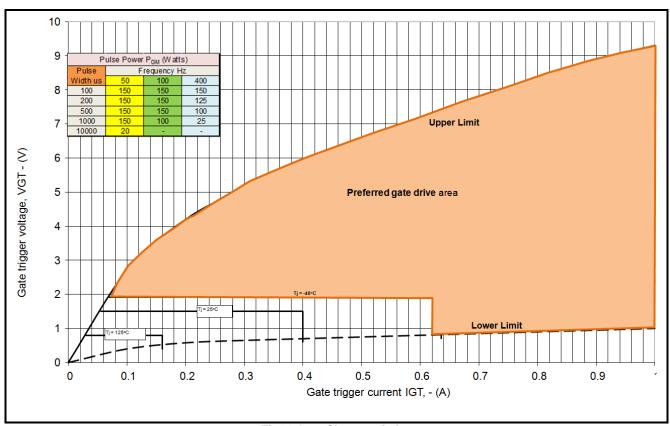


Fig14 Gate Characteristics

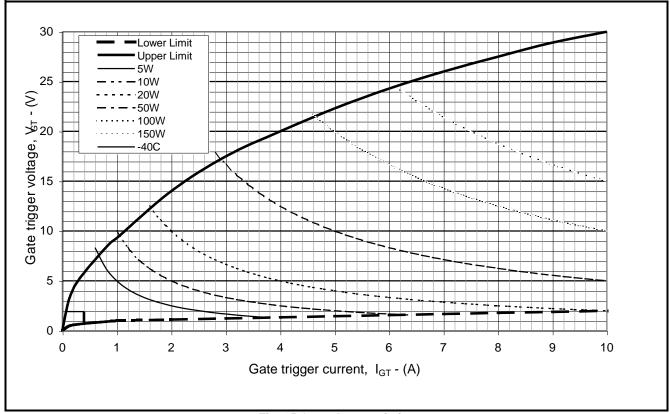


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

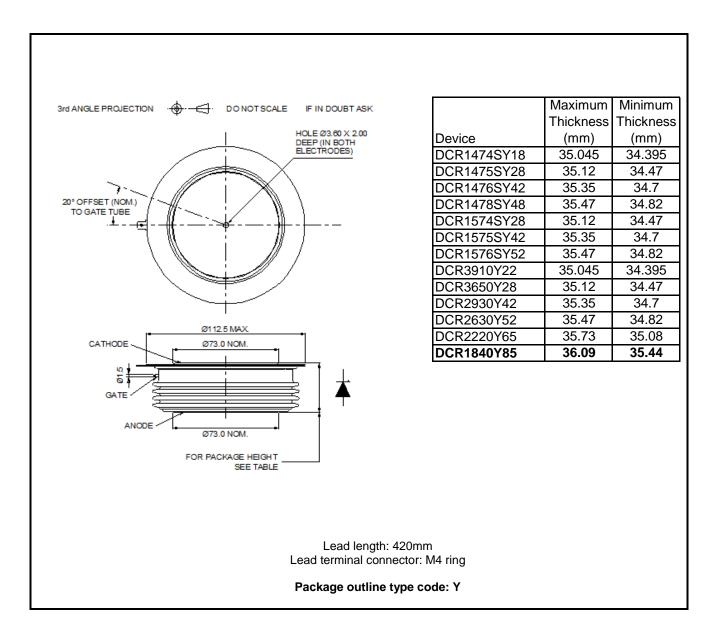


Fig.16 Package outline





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